

RF Power Field Effect Transistor

N-Channel Enhancement-Mode Lateral MOSFET

Designed for W-CDMA base station applications with frequencies from 2110 to 2170 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN-PCS/cellular radio and WLL applications.

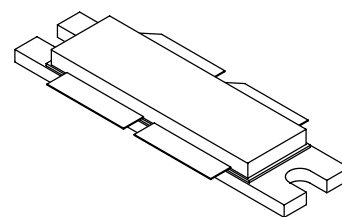
- Typical 2-Carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 2200$ mA, $P_{out} = 52$ Watts Avg., $f = 2157.5$ MHz, Channel Bandwidth = 3.84 MHz, PAR = 8.5 dB @ 0.01% Probability on CCDF.
Power Gain — 13 dB
Drain Efficiency — 24%
IM3 @ 10 MHz Offset — -36 dBc in 3.84 MHz Channel Bandwidth
ACPR @ 5 MHz Offset — -39 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 5:1 VSWR, @ 28 Vdc, 2140 MHz, 180 Watts CW Output Power

Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Low Gold Plating Thickness on Leads, 40 μ " Nominal.
- RoHS Compliant
- In Tape and Reel. R6 Suffix = 150 Units per 56 mm, 13 inch Reel.

MRF5P21240HR6

**2110-2170 MHz, 52 W AVG., 28 V
2 x W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFET**



**CASE 375D-05, STYLE 1
NI-1230**

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	603 3.4	W W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to +150	$^\circ\text{C}$
Case Operating Temperature	T_C	150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$
CW Operation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	CW	200 1.18	W W/ $^\circ\text{C}$

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 82°C , 180 W CW Case Temperature 77°C , 52 W CW	$R_{\theta JC}$	0.29 0.32	$^\circ\text{C}/\text{W}$

1. MTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model (per JESD22-A114)	2 (Minimum)
Machine Model (per EIA/JESD22-A115)	M3 (Minimum)
Charge Device Model (per JESD22-C101)	C6 (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics ⁽¹⁾					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ⁽¹⁾ ($V_{DS} = 10\text{ Vdc}$, $I_D = 300\ \mu\text{Adc}$)	$V_{GS(th)}$	2	2.8	4	Vdc
Gate Quiescent Voltage ⁽³⁾ ($V_{DS} = 28\text{ Vdc}$, $I_D = 2200\text{ mAdc}$)	$V_{GS(Q)}$	3	3.8	5	Vdc
Drain-Source On-Voltage ⁽¹⁾ ($V_{GS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	$V_{DS(on)}$	—	0.26	0.3	Vdc
Forward Transconductance ⁽¹⁾ ($V_{DS} = 10\text{ Vdc}$, $I_D = 3\text{ Adc}$)	g_{fs}	—	7.5	—	S

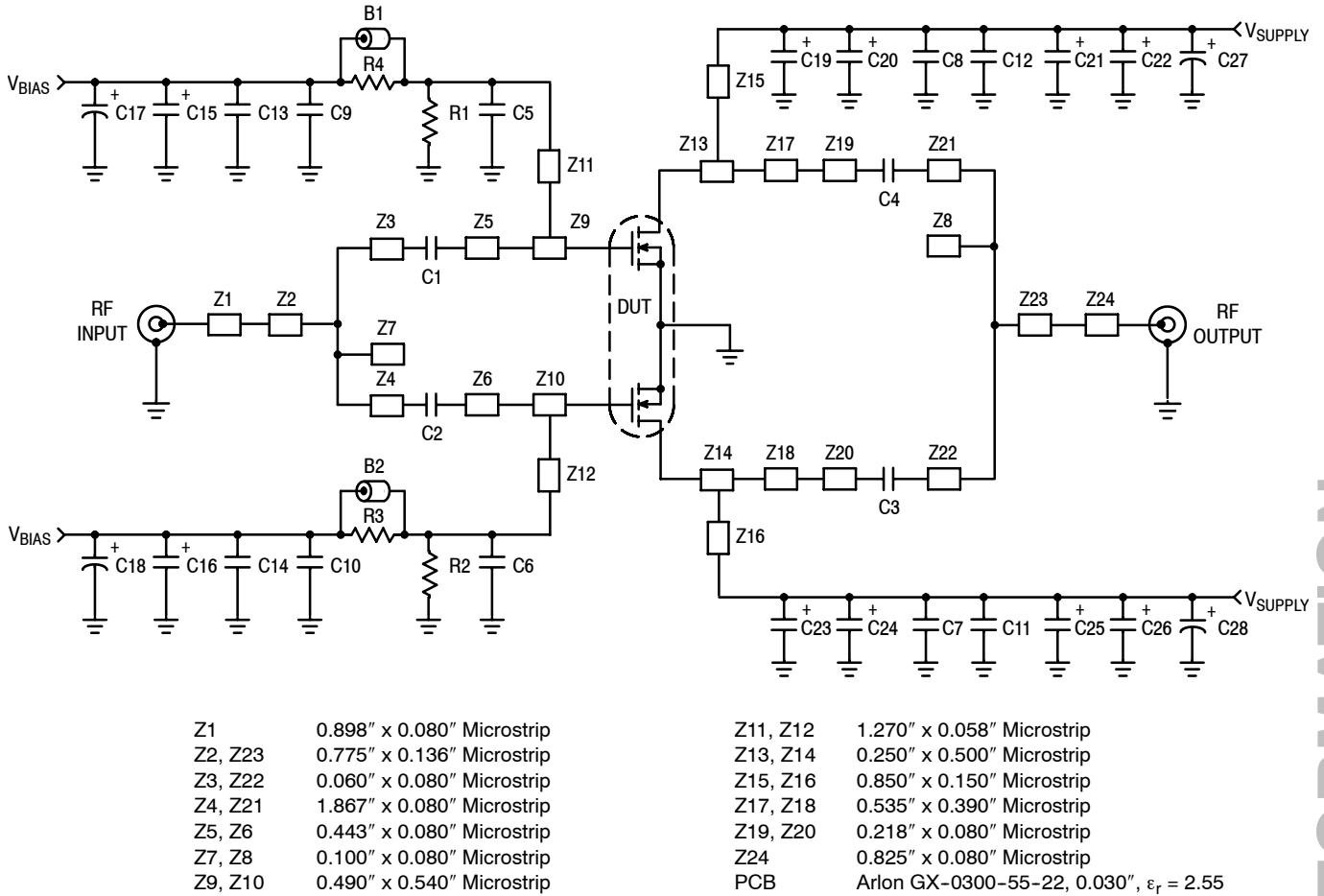
Dynamic Characteristics ^(1,2)

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0$, $f = 1\text{ MHz}$)	C_{rss}	—	2.75	—	pF
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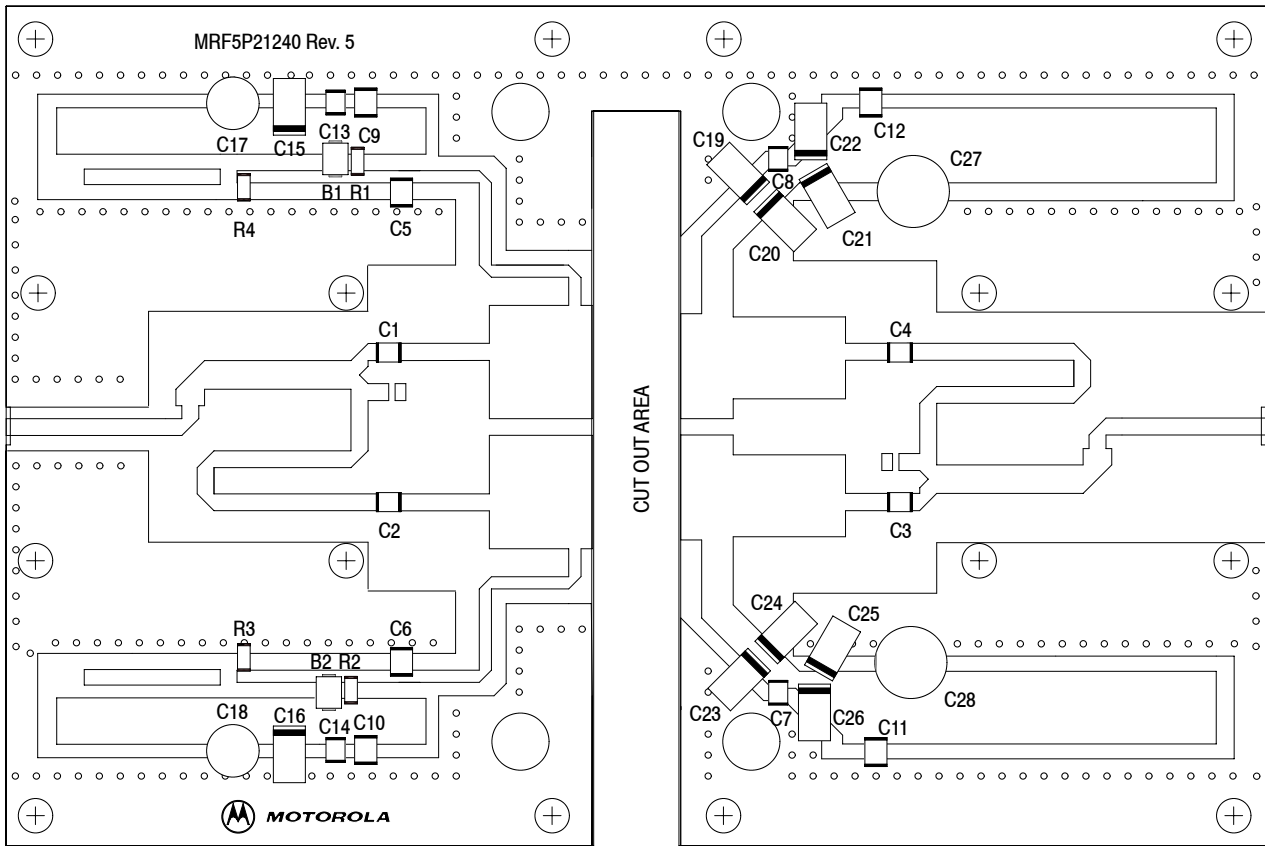
Functional Tests ⁽³⁾ (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 2200\text{ mA}$, $P_{out} = 52\text{ W Avg.}$, $f_1 = 2157.5\text{ MHz}$, $f_2 = 2167.5\text{ MHz}$, 2-Carrier W-CDMA, 3.84 MHz Channel Bandwidth Carriers. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset. IM3 measured in 3.84 MHz Bandwidth @ $\pm 10\text{ MHz}$ Offset. PAR = 8.5 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	12	13	—	dB
Drain Efficiency	η_D	22.5	24	—	%
Intermodulation Distortion	IM3	—	-36	-34	dBc
Adjacent Channel Power Ratio	ACPR	—	-39	-37	dBc
Input Return Loss	IRL	—	-12	-9	dB

1. Each side of device measured separately.
2. Part internally matched both on input and output.
3. Measurement made with device in push-pull configuration.


Figure 1. MRF5P21240HR6 Test Circuit Schematic
Table 5. MRF5P21240HR6 Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1, B2	Short Ferrite Beads	2743019447	Fair-Rite
C1, C2, C3, C4	18 pF Chip Capacitors	ATC100B180JCT500XT	ATC
C5, C6, C7, C8	6.8 pF Chip Capacitors	ATC100B6R8JCT500XT	ATC
C9, C10, C11, C12	0.1 μ F Chip Capacitors	CDR33BX104AKWS	Kemet
C13, C14	1000 pF Chip Capacitors	ATC100B102JCT500XT	ATC
C15, C16	4.7 μ F Tantalum Capacitors	T491C475M050AT	Kemet
C17, C18	10 μ F, 50 V Electrolytic Capacitors	EMVY500ADA100MF55G	Nippon Chemi-Con
C19, C20, C21, C22 C23, C24, C25, C26	22 μ F Tantalum Capacitors	T491X226K035	Kemet
C27, C28	100 μ F, 50 V Electrolytic Capacitors	EMVY500ADA101MHA0G	Nippon Chemi-Con
R1, R2	1 k Ω , 1/4 W Chip Resistors	CRCW12061001FKEA	Vishay
R3, R4	10 Ω , 1/4 W Chip Resistors	CRCW120610R0FKEA	Vishay



Freescle has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescle Semiconductor signature/logo. PCBs may have either Motorola or Freescle markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF5P21240HR6 Test Circuit Component Layout

TYPICAL CHARACTERISTICS

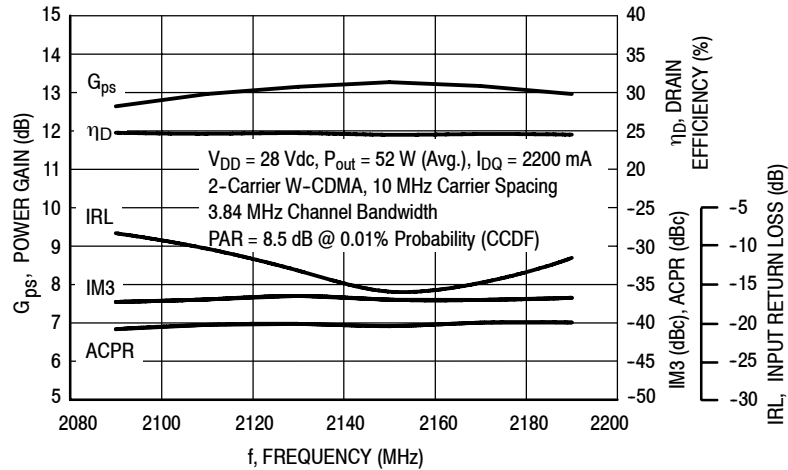


Figure 3. 2-Carrier W-CDMA Broadband Performance @ P_{out} = 52 Watts Avg.

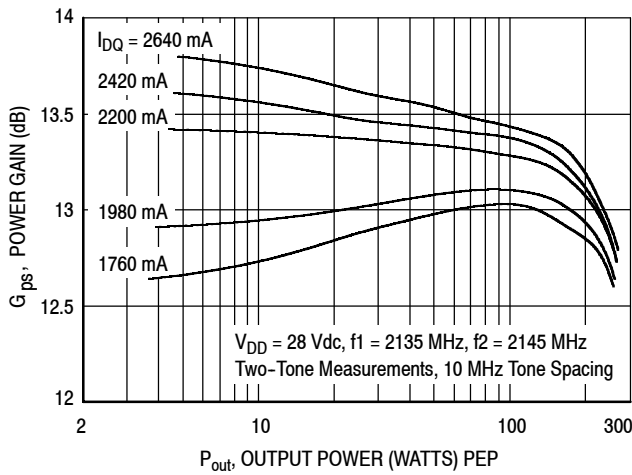


Figure 4. Two-Tone Power Gain versus Output Power

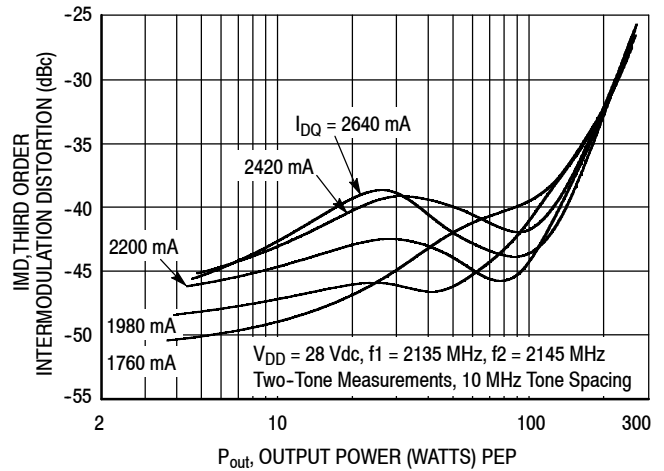


Figure 5. Third Order Intermodulation Distortion versus Output Power

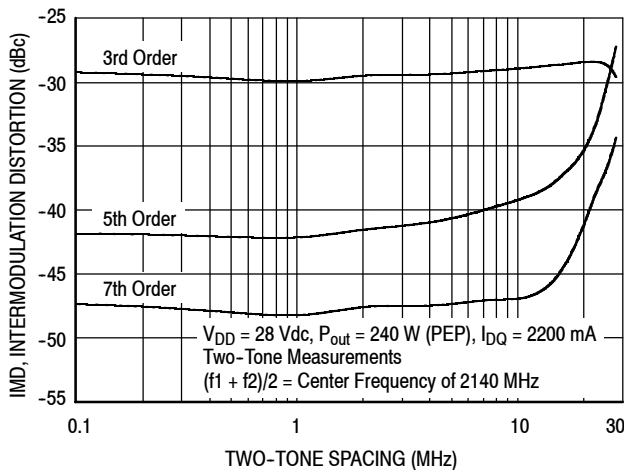


Figure 6. Intermodulation Distortion Products versus Tone Spacing

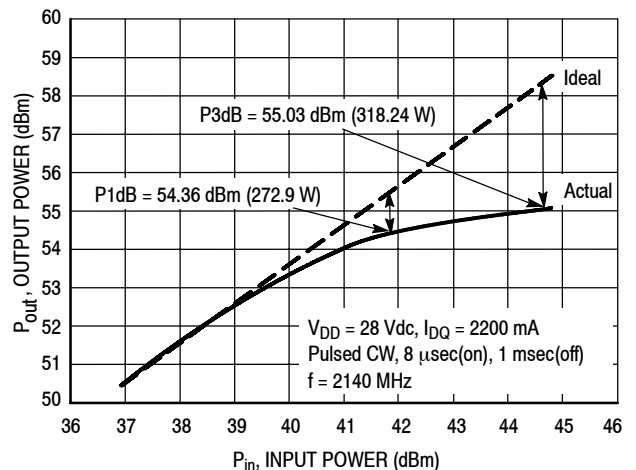


Figure 7. Pulse CW Output Power versus Input Power

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TYPICAL CHARACTERISTICS

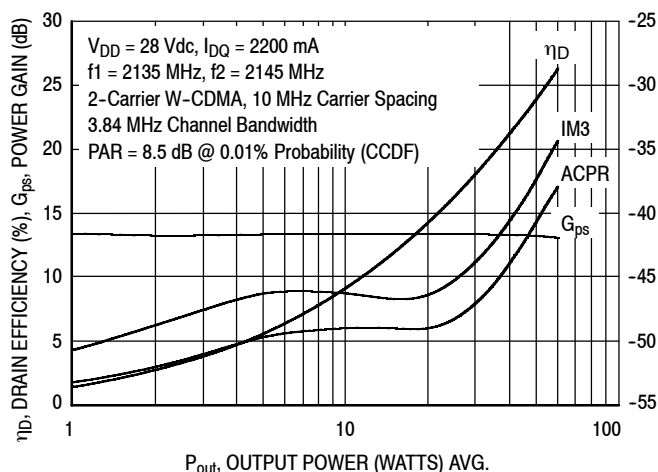
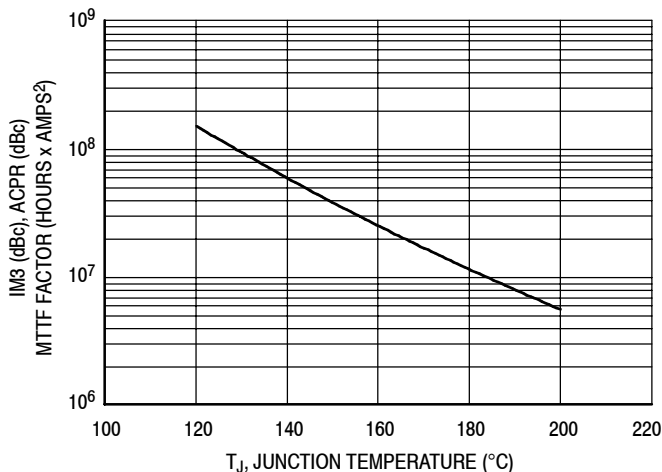


Figure 8. 2-Carrier W-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power



This above graph displays calculated MTTF in hours x ampere² drain current. Life tests at elevated temperatures have correlated to better than ±10% of the theoretical prediction for metal failure. Divide MTTF factor by I_D^2 for MTTF in a particular application.

Figure 9. MTTF Factor versus Junction Temperature

W-CDMA TEST SIGNAL

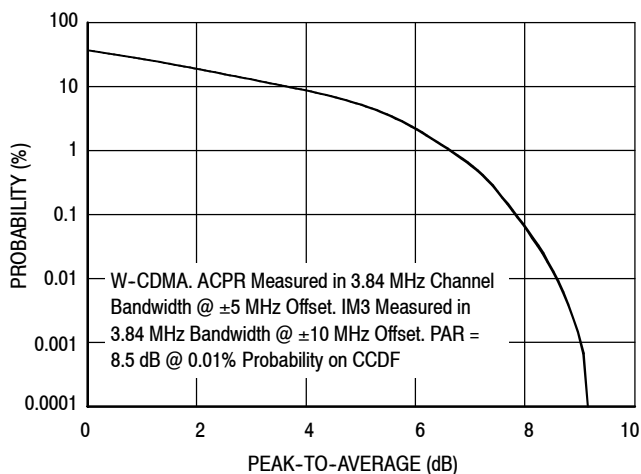


Figure 10. CCDF W-CDMA 3GPP, Test Model 1, 64 DPCH, 67% Clipping, Single-Carrier Test Signal

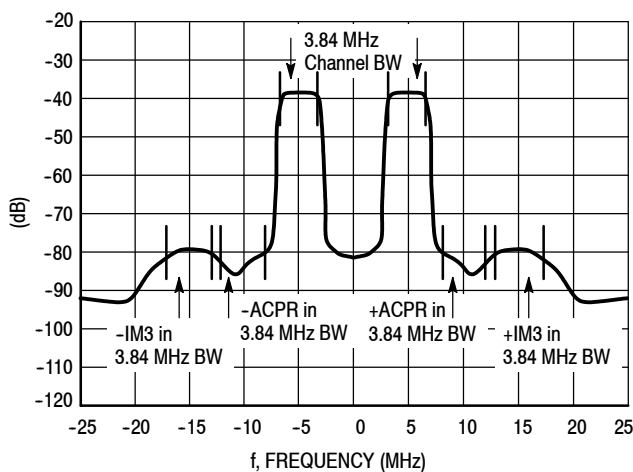
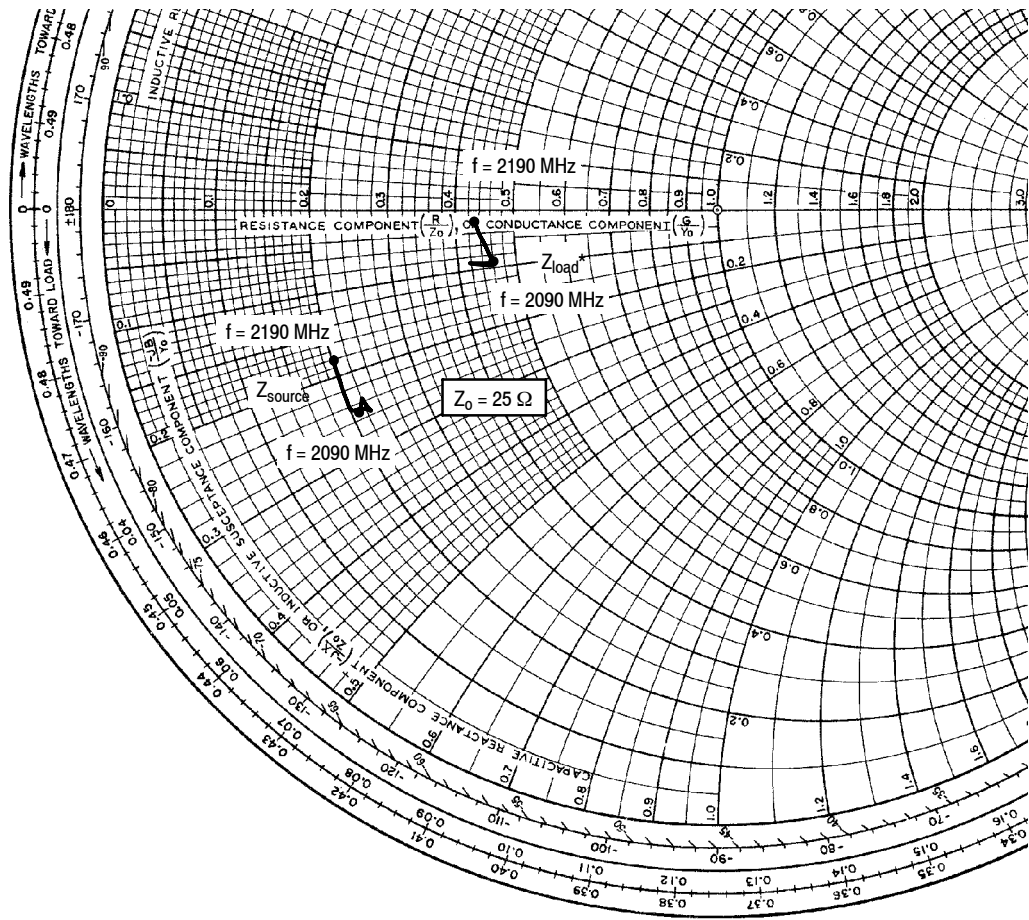


Figure 11. 2-Carrier W-CDMA Spectrum

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$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 2200 \text{ mA}$, $P_{out} = 52 \text{ W Avg.}$

f MHz	Z _{source} Ω	Z _{load} Ω
2090	5.33 - j6.21	11.42 - j2.25
2110	5.44 - j5.88	10.45 - j2.16
2130	5.40 - j6.16	11.28 - j2.14
2150	5.12 - j6.06	11.38 - j2.14
2170	4.96 - j5.25	11.04 - j1.25
2190	4.98 - j4.47	10.73 - j0.40

Z_{source} = Test circuit impedance as measured from gate to gate, balanced configuration.

Z_{load} = Test circuit impedance as measured from drain to drain, balanced configuration.

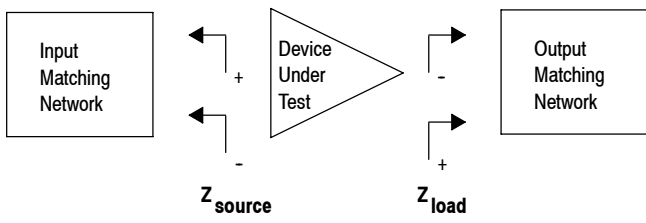
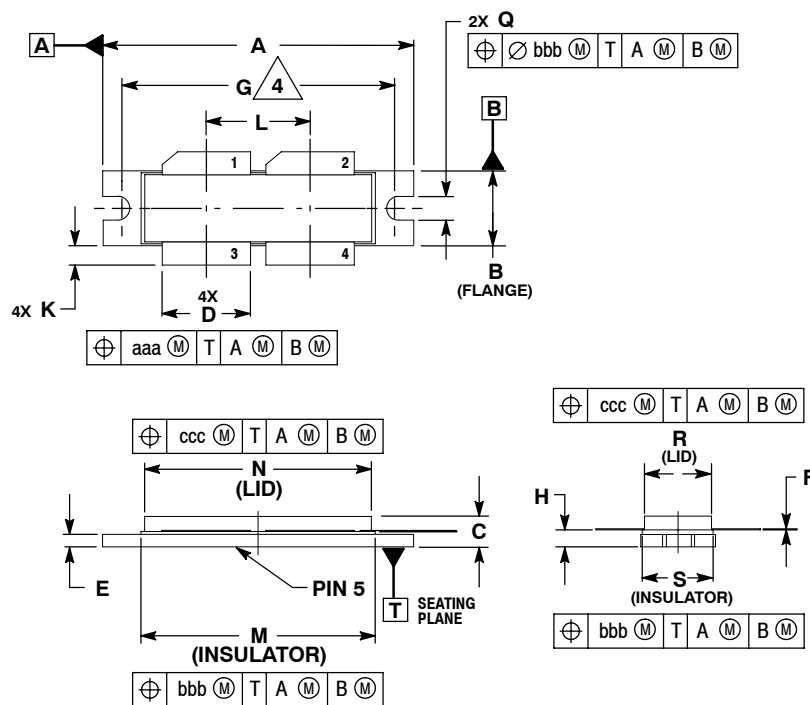


Figure 12. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



- NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
 4. RECOMMENDED BOLT CENTER DIMENSION OF 1.52 (38.61) BASED ON M3 SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.28
B	0.395	0.405	10.03	10.29
C	0.150	0.200	3.81	5.08
D	0.455	0.465	11.56	11.81
E	0.062	0.066	1.57	1.68
F	0.004	0.007	0.10	0.18
G	1.400 BSC		35.56 BSC	
H	0.082	0.090	2.08	2.29
K	0.117	0.137	2.97	3.48
L	0.540 BSC		13.72 BSC	
M	1.219	1.241	30.96	31.52
N	1.218	1.242	30.94	31.55
Q	0.120	0.130	3.05	3.30
R	0.355	0.365	9.01	9.27
S	0.365	0.375	9.27	9.53
aaa	0.013 REF		0.33 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.020 REF		0.51 REF	

- STYLE 1:
 PIN 1. DRAIN
 2. DRAIN
 3. GATE
 4. GATE
 5. SOURCE

CASE 375D-05
 ISSUE E
 NI-1230

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
2	Oct. 2008	<ul style="list-style-type: none"> • Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN12779, p. 1, 2 • Updated Part Numbers in Table 5, Component Designations and Values, to RoHS compliant part numbers, p. 3 • Added Product Documentation and Revision History, p. 9 • Data sheet archived. Part no longer manufactured.

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